

## **isc Silicon NPN Power Transistor**

# BUX84F

### DESCRIPTION

- Collector-Emitter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub>= 400V(Min.) • High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

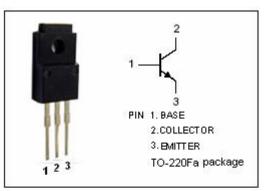
• Designed for use in high-voltage,high-speed,power switching regulators,converters,inverters,motor control system.

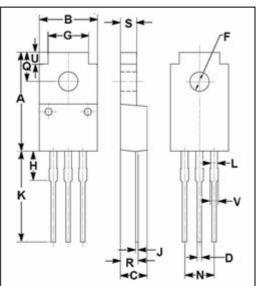


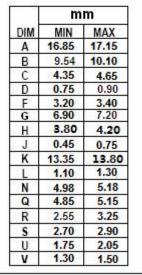
SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CES</sub>	Collector-Emitter Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
Ic	Collector Current-Continuous	2	А
Ісм	Collector Current-Peak	3	А
I <sub>B</sub>	Base Current	0.75	А
I <sub>BM</sub>	Base Current-Peak	1	А
Pc	Collector Power Dissipation @T <sub>c</sub> =25°C	18	W
Tj	Junction Temperature	perature 150	
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance, Junction to Case	7.2	℃/W







isc website: <u>www.iscsemi.com</u>



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## **ELECTRICAL CHARACTERISTICS**

### $T_{c}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	400			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.3A; I <sub>B</sub> = 0.03A			0.8	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.1	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0 V <sub>CB</sub> = 800V; I <sub>E</sub> = 0;T <sub>C</sub> =125℃			0.2 1.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	Ic= 0.1A; Vce= 5V	20		100	
hfe-2	DC Current Gain	Ic= 0.5A; Vce= 5V	15			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V, f <sub>test</sub> = 1MHz		20		MHz

### **NOTICE:**

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